

Cadence Transistor-Level EMIR Solution

Voltus-Fi Custom Power Integrity Solution

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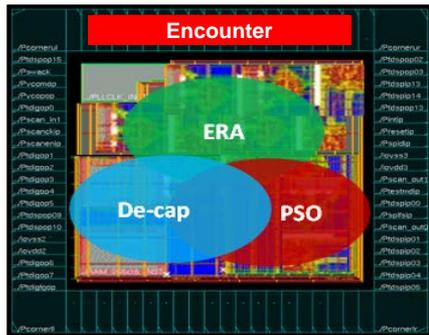
Agenda

- Introduction -- Cadence Power Signoff Solution
- Transistor-Level EMIR Challenges and Cadence Advantages
- Visualization, Analysis & Debug
- Summary

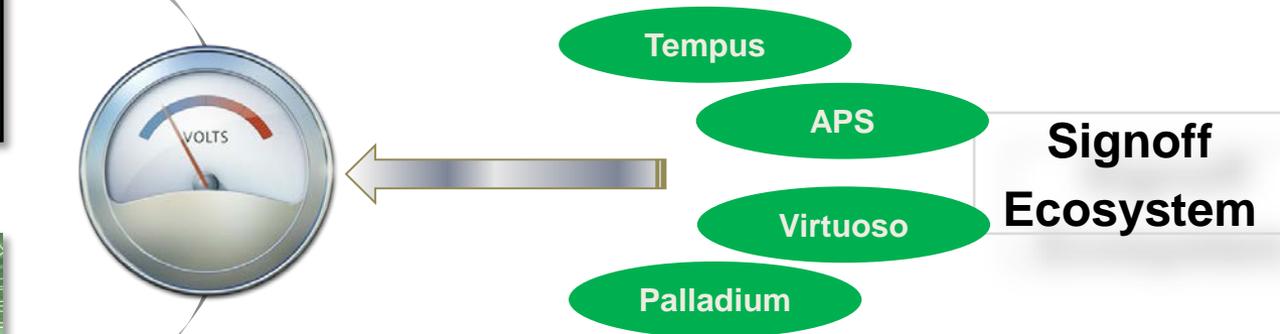
Introduction – Cadence Power Signoff Solution

Voltus – Fast Design Closure

Complete Design Flow from Chip to System



- Tight Integration with IC Physical Implementation
 - Early rail analysis & ECO: during power planning stages
 - De-cap & ECO: IR-drop and leakage reduction
 - Power gate switching & ECO: rush current, turn-on time



- Chip-package-PCB Co-Simulation and Analysis
 - Accurate power grid networks for chip and board
 - Electrical-Thermal analysis
 - 3DIC support, including CoWoS (2.5D)

Productivity Improvements in IC Design Closure and System Design

Voltus IC Power Integrity Solution

- Breakthrough **massively parallel** execution technology in SoC power signoff
- Up to 10X faster performance gain over existing solutions
- Capacity up to **1 billion** instances with hierarchical analysis capability
- Integrated with key Cadence® technology for fast design signoff and closure
- Certified for TSMC 10nm FinFET+ process



Performance, accuracy, and design closure

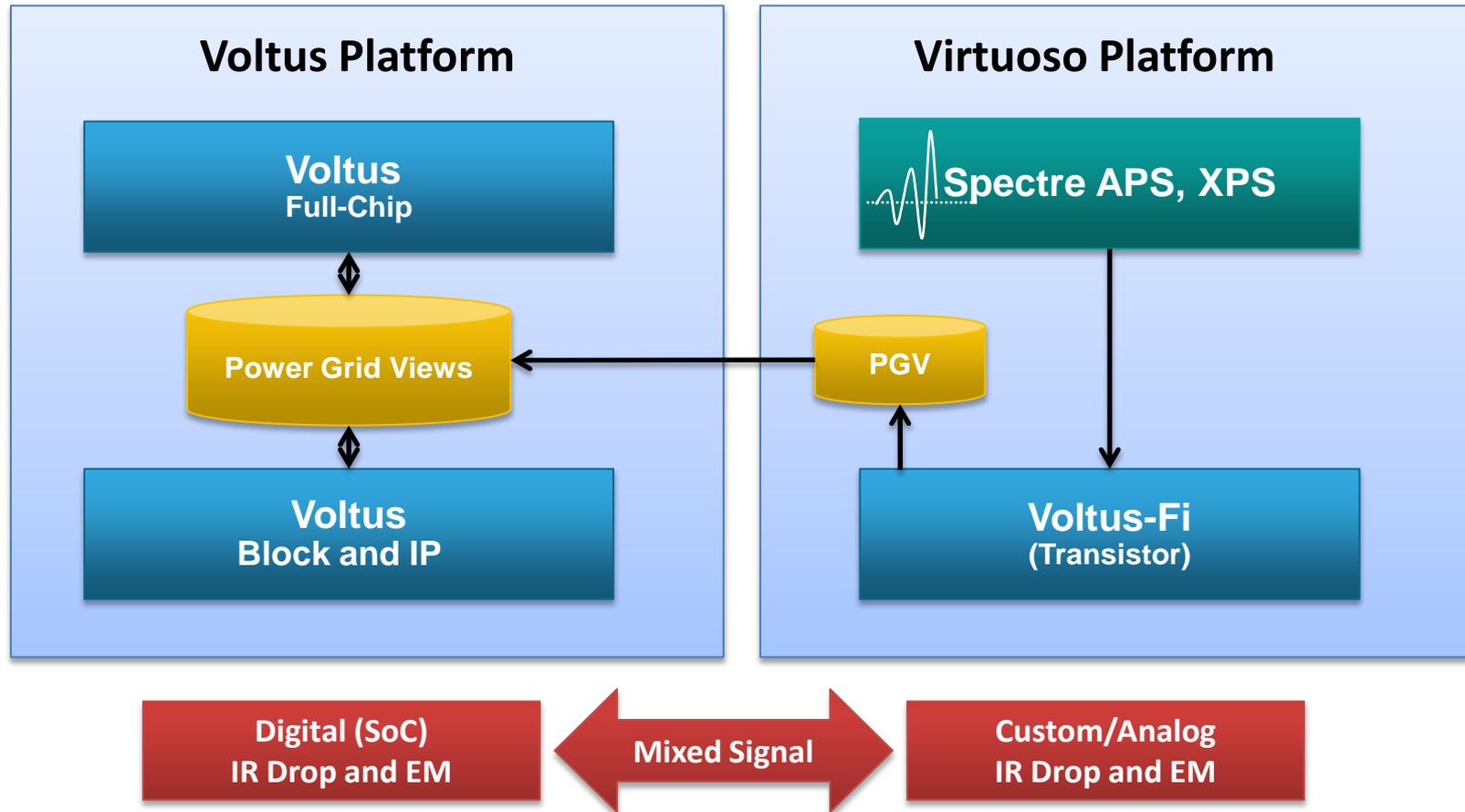
Voltus-Fi Custom Power Integrity Solution

- Complete Cadence® IC power signoff platform in “Voltus™ + Voltus-Fi”
- TSMC 10nmFF+ certified, SPICE-accurate transistor-level power signoff
- Industry’s only fully integrated solution in Virtuoso® platform for superior ease-of-use
- Seamless flow in Voltus-Fi to Voltus for accurate full-chip level SoC power signoff
- Tight integration with Cadence’s tools for accuracy, performance, and fast design closure



Fastest path to accurate analog/mixed-signal power signoff

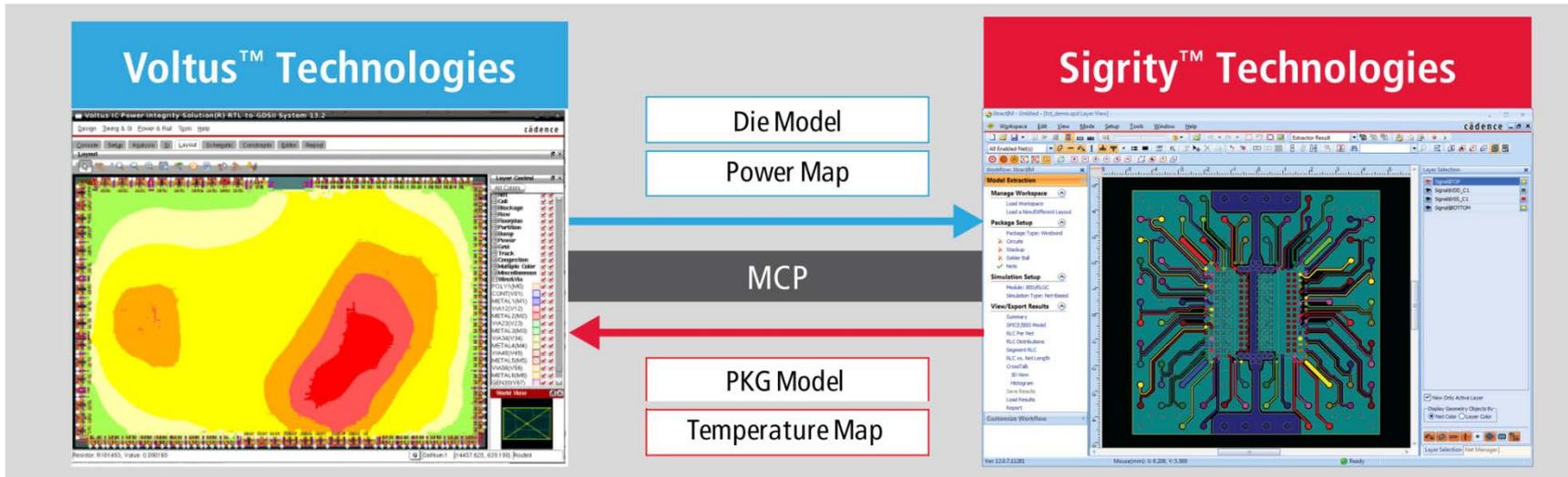
Voltus-Fi Custom Power Integrity Solution



Accurate Transistor EMIR Analysis, High-quality Analog IP Grid Modeling

Voltus and Sigrity Chip-PKG-PCB Co-Analysis

- Accurate Power Signoff for Highly Coupled Power Delivery Network



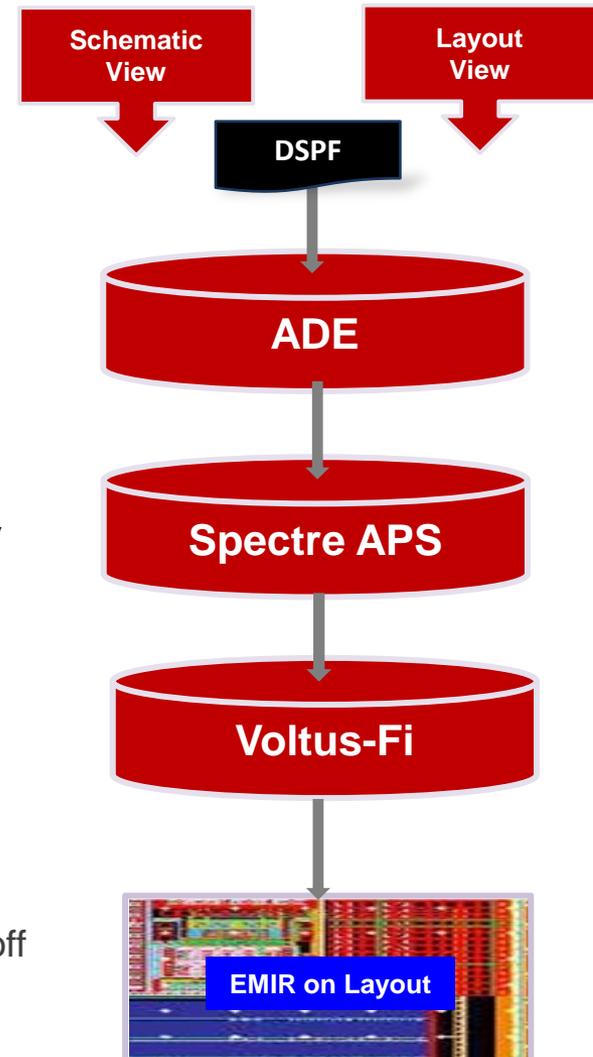
- Die-model and PKG / PCB-model in broadband SPICE format for “Voltus™ + Sigrity™” co-analysis
- Power map / temperature map for electro-thermal co-analysis
- Comprehensive power and signal integrity analysis including IO-SSO

3D-IC technology, Multi-chip Modules, Single/Stacked-die in Package

Competitive Advantages

- Cadence Offers a Complete Solution
 - Layout and parasitic **Extraction**
 - Transistor level EMIR **Simulation**
 - EMIR **Visualization**, analysis, debug and fix
 - An **Integrated** flow for high QoR
- Proprietary Technology in MMSIM Spectre APS|XPS EMIR Algorithm
 - Patented voltage-based “iterated” method in power network RC solving
- Comprehensive EMIR Result Analysis Capability in Voltus-Fi Flow
 - Foundry certification
 - Quantus QRC: extraction accuracy
 - APS: simulation accuracy
 - Voltus-Fi: EM rules and IR-drop accuracy
 - Integration with Virtuoso from ADE to VLS for greater design productivity
 - PGV generation for full-chip level SoC Voltus power signoff

Cadence Voltus-Fi EMIR Flow

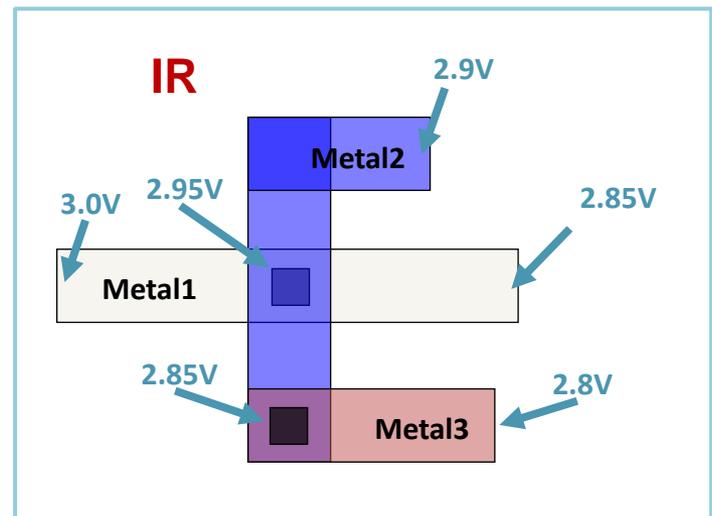
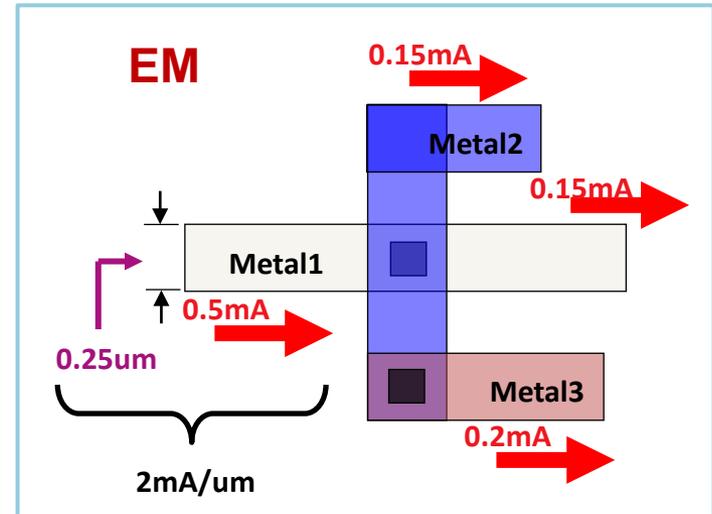


Transistor-level Electro-Migration & IR-Drop

Challenges and Cadence Advantages

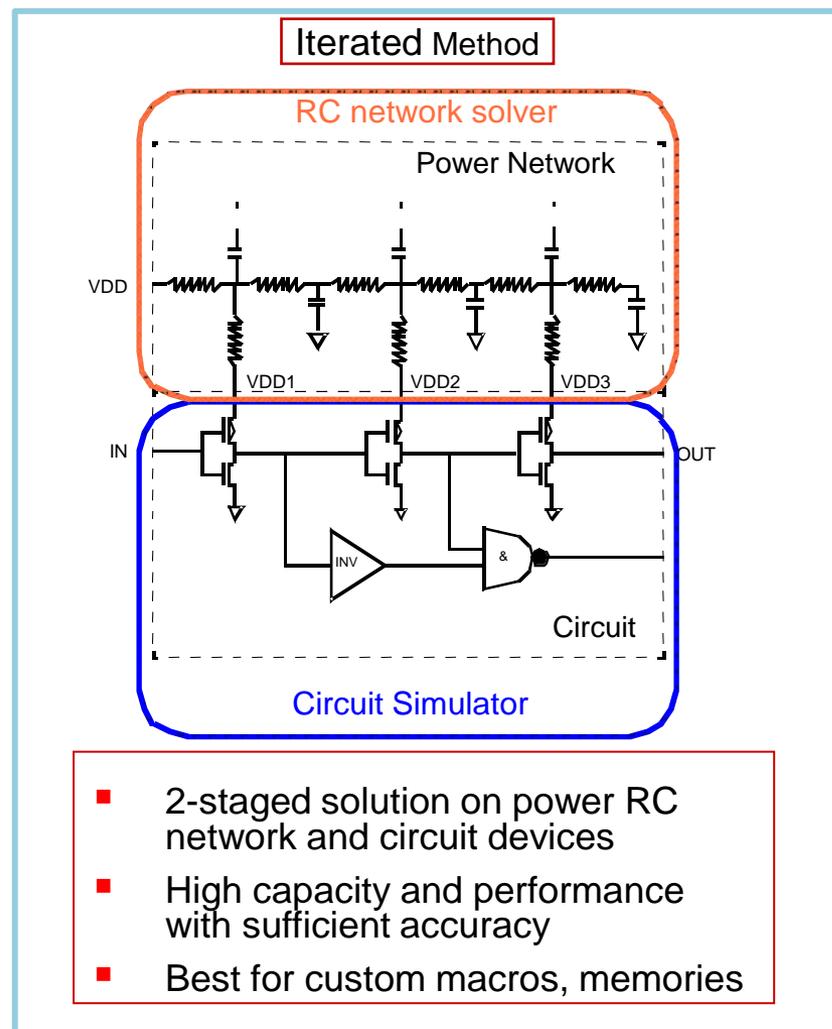
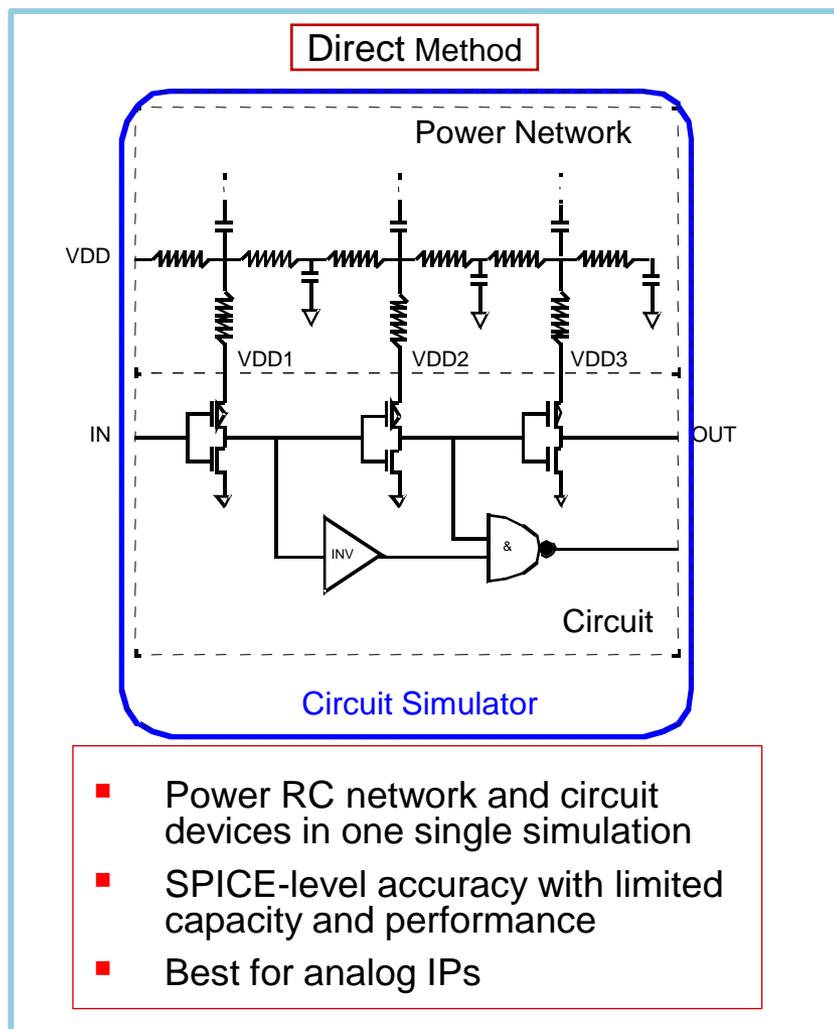
Transistor-Level EMIR Analysis

- EM Analysis
 - High density current in a narrow metal wire may destroy the wire by electron migration
 - An EM analysis solution calculates current and compares to EM rules on each wire
 - Advanced nodes, especially on FinFET, have very complex EM rules such as wire length, width, current direction dependency
- IR Analysis
 - Voltage drop along the metal wire may cause signal integrity issue or even functional failure
 - An IR analysis solution calculates voltage and ensures its sufficiency to meet specification
- Unique Challenges in Tx-level EMIR
 - Simulation on large RC network from post-layout for “current” is very expensive
 - Ease-of-Use for quick analysis, debug and fix on a familiar design GUI platform
 - Unified power signoff: “cell + trx” for full-chip SoC



Solving Power Network RC Matrix

- Direct and Iterated Method



Benchmark Examples

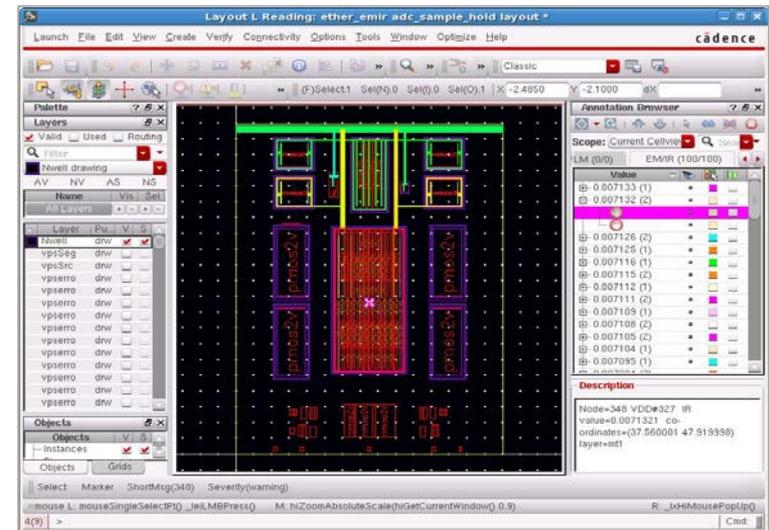
- Power Net EMIR and Signal EM Analysis

	Statics	16Kx32-byte-data (90nm)	32K-SRAM (20nm)
Circuit Inventory	MOS	3,226K	~2,000K
	Diode	297	210
	R	25,240K	120M
	C	16,427K	85M
	Nodes	1,072K	605K
Transient Time		5ns	16ns
Simulator		APS	APS
Total Runtime		4h10m	7h36m
Peak Memory		97GB	120G

Visualization, Analysis & Debug

Design Input Data Requirements

- Design Data
 - xDSPF of the design
 - Decoupled RC extracted for all nets, including PG nets
 - With physical information for layers
 - Testbench schematic or netlist
 - DFII schematic for Virtuoso® Analog Design Environment based simulation
 - DFII layout for results visualization and structural checks or GDSII of the design with layer map to pipe it in Virtuoso platform
- Technology Data
 - SPICE models and corners
 - DFII technology library
 - ICT file or qrcTechFile with EM models



EMIR Result Analysis in Voltus-Fi

- Launching Voltus-Fi from Virtuoso Layout View
- Enabling Violations Browser for IR Violations and EM Violation
- Cross-probing between Graphic Display and Simulation Text Report

The image displays the Voltus-Fi software interface for analyzing IR and EM violations. The main window shows a layout titled "Layout L Reading: Two_Stage_Opamp DiffOpAmp layout (on euvcl034)". The interface includes a menu bar, a toolbar, and a palette. The layout itself is a complex circuit board design with various colored regions and traces.

Two browser windows are open, displaying simulation reports in HTML format. The "IR report" window shows the following data:

Net Name	Vmax
avss	maxV = 2.096mV Vref = 0.63V
avdd	maxV = 4.326mV Vref = 0.63V

The "EM report" window shows a table of net names, layer names, and IRMS values:

Net Name	layer	IRMS
avss	met1_2_028m	IRMS = 2.232mA
avss	met1_1_0417m	IRMS = 1.983mA
avss	met1_0_090m	IRMS = 308.090mA
avss	met1_0_0270m	IRMS = 1.983mA
avss	met1_0_080m	IRMS = 36.002mA
avss	met1_0_085m	IRMS = 1.983mA
avss	met1_0_112m	IRMS = 55.233mA
avss	met1_0_112m	IRMS = 1.983mA
avss	met1_0_127m	IRMS = 1.983mA
avss	met1_0_127m	IRMS = 389.086mA
avss	met1_0_122m	IRMS = 1.983mA
avss	met1_0_134m	IRMS = 33.249mA
avss	met1_0_134m	IRMS = 1.983mA
avss	met1_0_174m	IRMS = 177.893mA
avss	met1_0_174m	IRMS = 177.893mA

The "IR/EM Results (on euvcl034)" window shows a "Results" section with a "Net Plot" table:

Net Type	Net Name
power	AVDD
power	AVSS

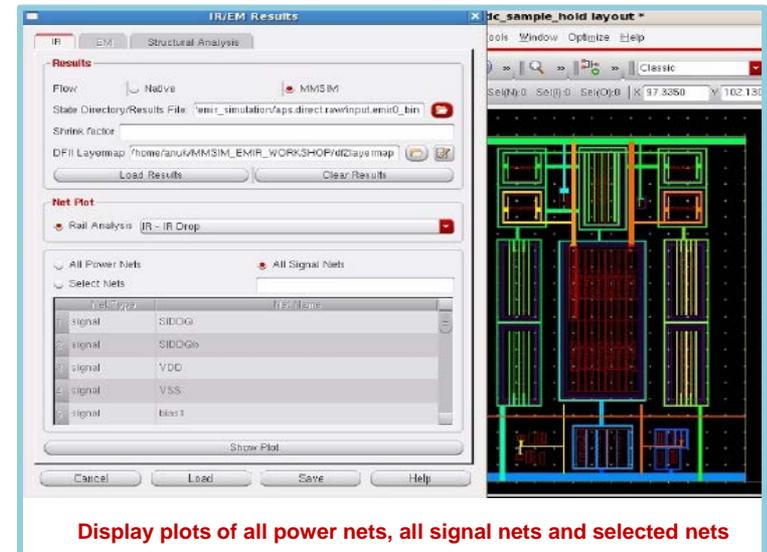
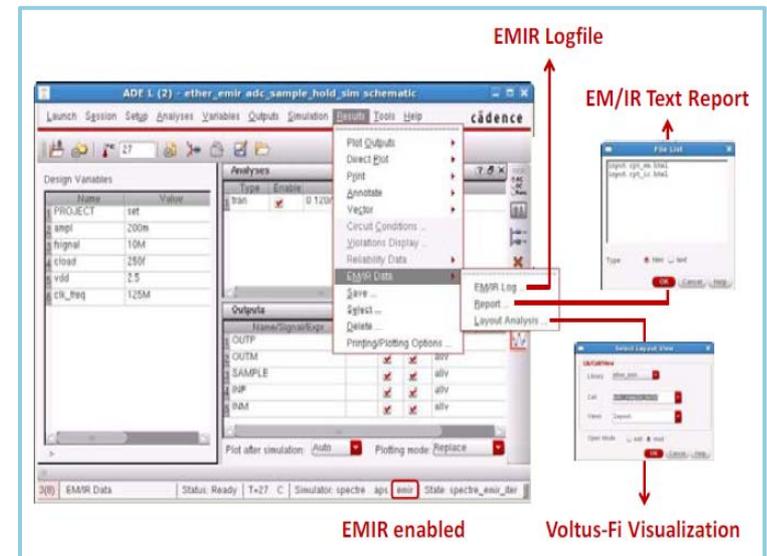
The "IR values in volts" window shows a color scale from 0 to 0.006533745. The "Layers" list includes: conf_diff, conf_pad, conf_poly, metal0_conn, metal1_conn, metal1_conn, metal2_conn, metal2_conn. The "Action" section includes: Violation Browser (Elements count: 100), Open Report after Saving, Save Report, Zoom Select Max Violation, Get Value on Layout, Save Plot, and Help.

A callout box labeled "HTML Format" points to the report windows.



Voltus-Fi Visualization

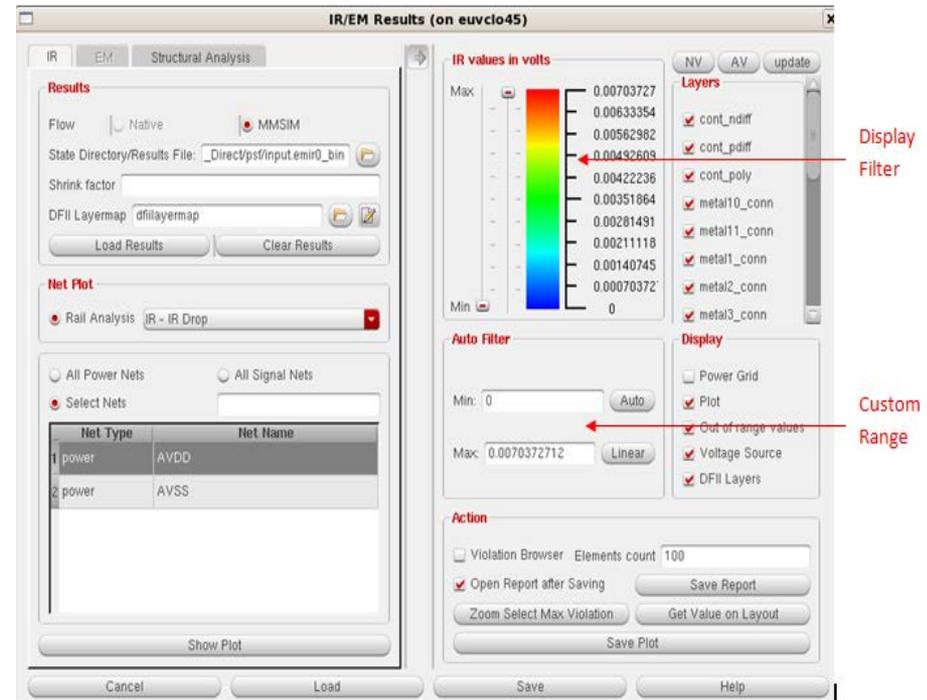
- Usability and Integration
 - Fully integrated with ADE simulation environment and Virtuoso Layout Editor
 - Plots are overlaid real time over the layout
 - Continuous 100 color filter to improve usability
 - Leverages existing Annotation Browser as Violation Browser
 - Querying the worst violation and worst violation in an area
- Varied EMIR Plots & Detailed EMIR Reports
 - Signal net IR-drop plot
 - Power gating switch analysis plots
- Structural Analysis
 - Early detection of certain EMIR root cause
- Transistor-level Block's PGV Generation
 - For Voltus top-level power signoff analysis



Display plots of all power nets, all signal nets and selected nets

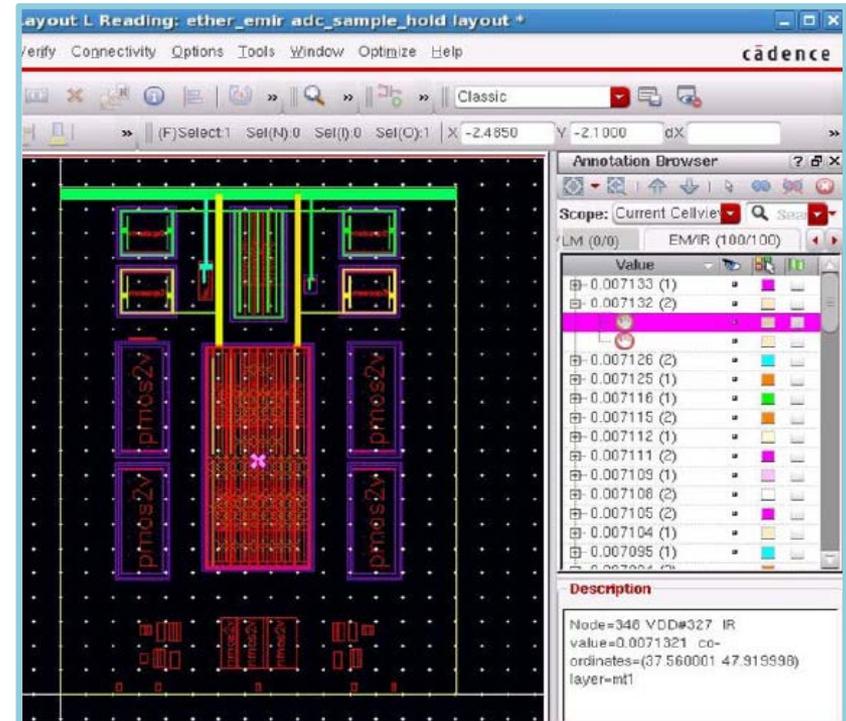
Ease-of-Setup and Rich Features

- The Continuous Filter has Sliders to change the Ranges
- Filters can be set from Fields as well
- The Display of the following can be easily toggled
 - DFII layers
 - Plots
 - Voltage sources
 - Out of range values
- User can also select the worst value in an area
- Layer Specific Results can also be displayed



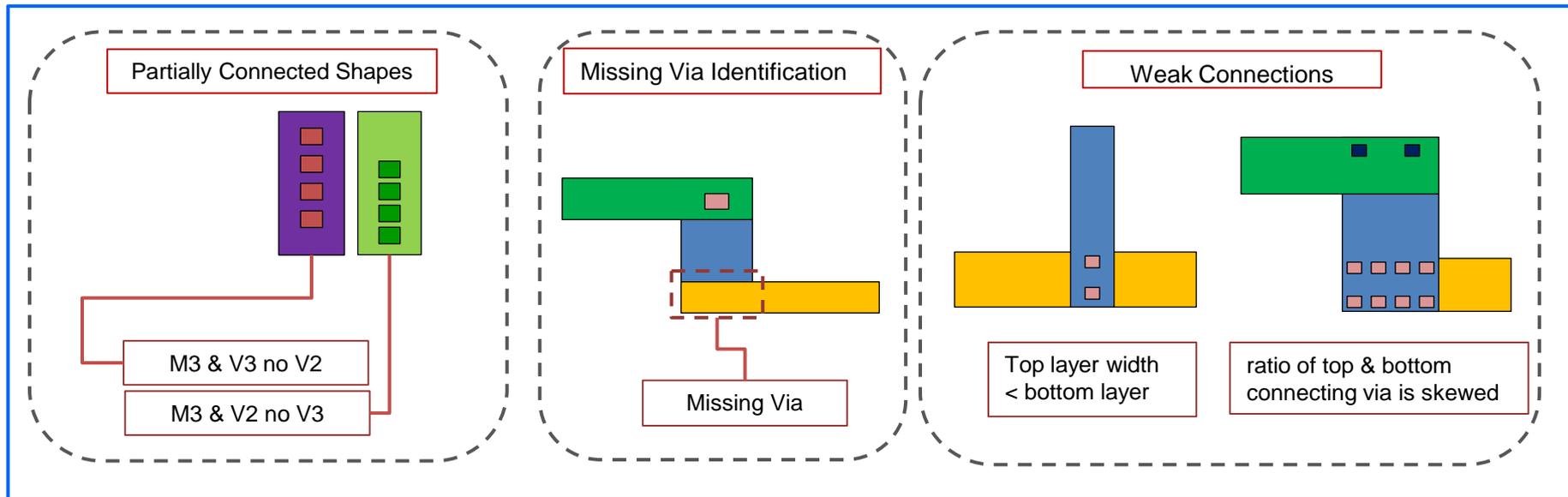
Violation Browser

- Violation Browser, by default, lists Top 100 Violations
- User can use Browser to zoom into the selected Violation
- It is, by default, docked inside the Virtuoso Main Window but can be undocked as well
- It has all the features in Annotation Browser



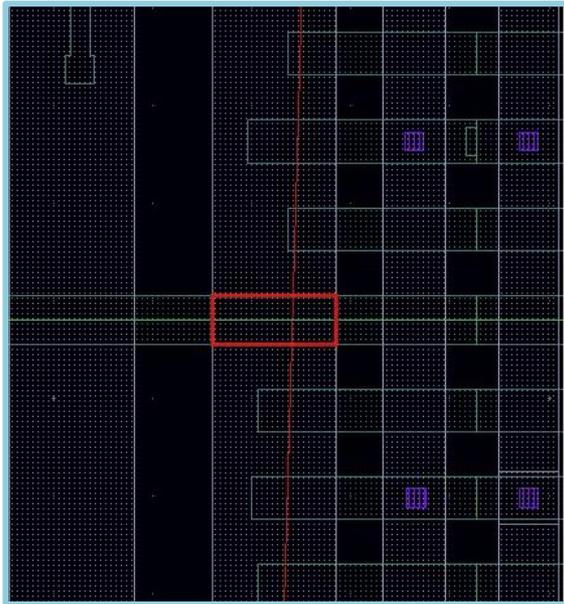
Shape-Based Geometrical Analysis

- To Quickly Identify Power Grid Weakness Through Voltus-Fi Visualization
- Structural Checks on Power Grid Nets
 - Partially connected or unconnected shapes in layout patterns
 - Top VIA missing, Bottom VIA missing
 - Overlapping layers
 - Missing VIA connections, VIA coverage ratio
 - Weakly connected shapes
 - Skewed VIA ratio



Structural Analysis

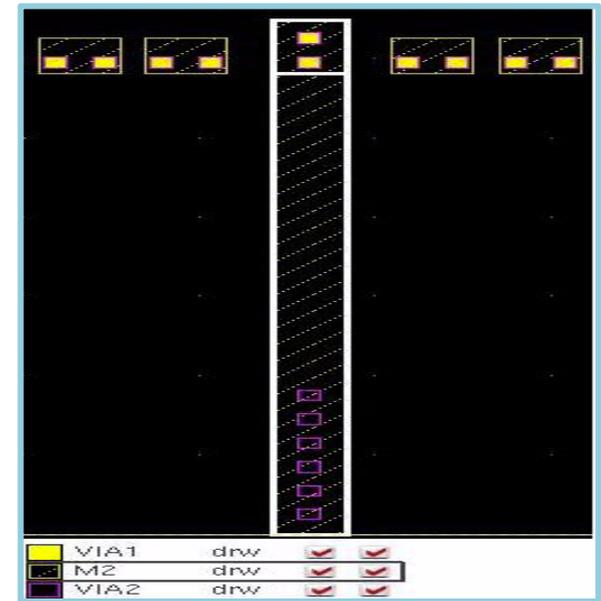
- Example



Missing VIA

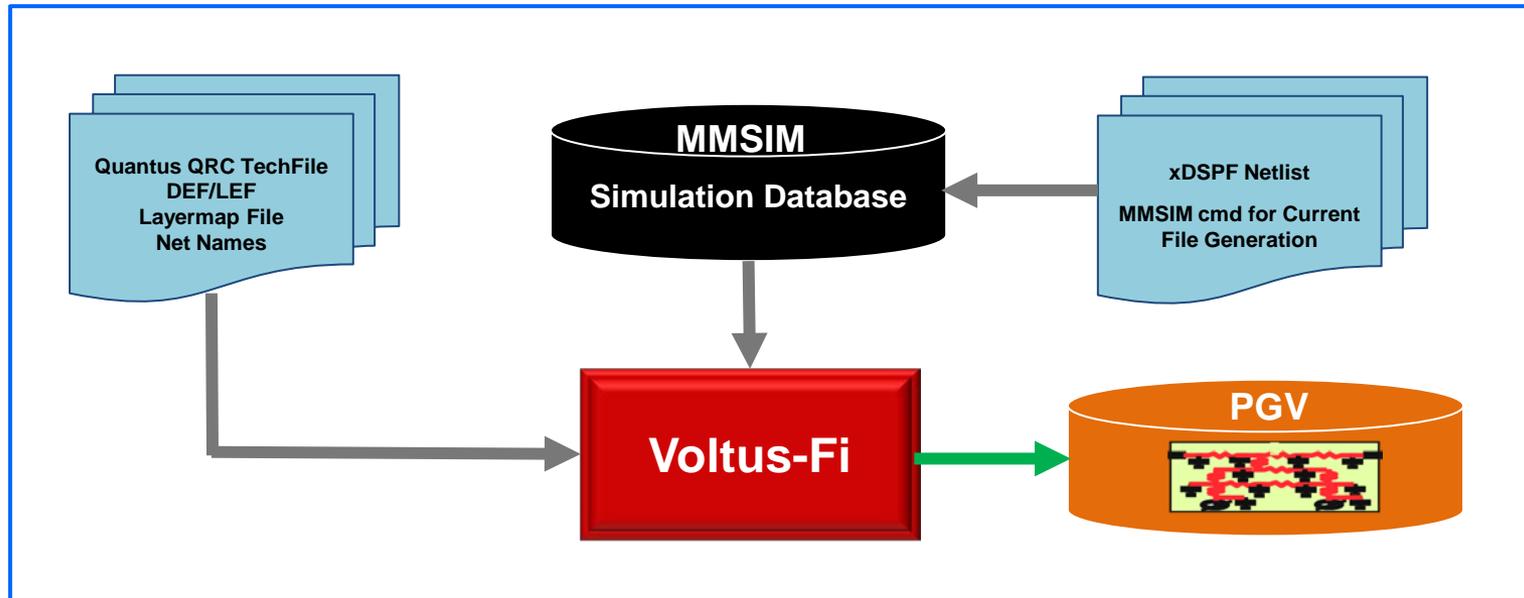


Via Coverage Ratio



Skewed VIA Ratio

Voltus-Fi on PGV Generation



- A Power-Grid-View (PGV) is a Binary Model for an IP's Grid Characteristic
 - Geometric views, port information
 - MMSIM setup for the current characterization of Power & Ground nets
 - Multi-mode feature in capturing various operational modes of an IP block
- An IP's PGV Should be Generated if a Significant Large P|G Nets are Shared Between Transistor-block and Cell-digital (Voltus)
 - Voltus top-level, full-chip power signoff

Summary

Summary

- Voltus is a complete solution in power integrity analysis and signoff
 - Voltus-Fi Custom Power Integrity Solution: Transistor-level power signoff
 - Voltus IC Power Integrity Solution: Cell-level SoC power signoff
- Voltus-Fi solution provides the most accurate transistor-level solution that is fully integrated in the Virtuoso platform
 - Performance and accuracy by Spectre APS/XPS
 - Visualization, debugging, and fixing in Virtuoso platform



Thanks